

January 1997

CD74FCT861A

BiCMOS FCT Interface Logic, 10-Bit Bus Transceiver, Three-State

Features

- Buffered Inputs
- Typical Propagation Delay: 6.0ns at $V_{CC} = 5V$, $T_A = 25^\circ C$, $C_L = 50pF$
- CD74FCT861A
 - Noninverting
- SCR Latchup Resistant BiCMOS Process and

**NOT RECOMMENDED
FOR NEW DESIGNS**
Use CMOS Technology

Circuit Design

- Speed of Bipolar FAST™/AS/S
- 48mA Output Sink Current
- Output Voltage Swing Limited to 3.7V at $V_{CC} = 5V$
- Controlled Output Edge Rates
- Input/Output Isolation to V_{CC}
- BiCMOS Technology with Low Quiescent Power

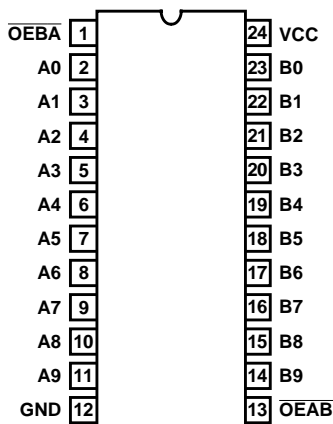
Ordering Information

| PART NUMBER | TEMP. RANGE ($^\circ C$) | PACKAGE | PKG. NO. |
|--------------|-------------------------------|------------|-------------|
| CD74FCT861AM | 0 to 70 | 24 Ld SOIC | M24.3 |

NOTE: When ordering the suffix M package, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.

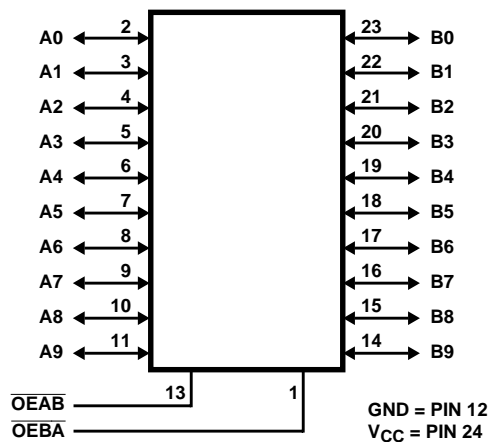
Pinout

CD74FCT861A
(SOIC)
TOP VIEW



CD74FCT861A

Functional Diagram



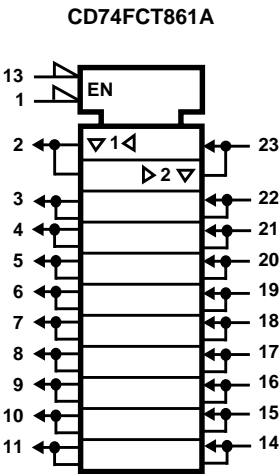
TRUTH TABLE (Note 1)

| INPUTS | | | | OUTPUTS | | FUNCTION |
|--------|------|-----|-----|---------|-----|-------------------------------------|
| OEBA | OEAB | B | A | B | A | |
| L | H | L | N/A | N/A | L | B Data to A Bus |
| L | H | H | N/A | N/A | H | B Data to A Bus |
| H | L | N/A | L | L | N/A | A Data to B Bus |
| H | L | N/A | H | H | N/A | A Data to B Bus |
| H | H | X | X | Z | Z | High Z |
| L | L | - | - | - | - | A Data to B Bus, B Data to A Bus |

NOTE:

- 1. H= HIGH Voltage Level
- L = LOW Voltage Level
- N/A = Not Applicable
- X = Immaterial
- Z = HIGH Impedance

IEC Logic Symbol



CD74FCT861A

Absolute Maximum Ratings

DC Supply Voltage (V_{CC}) -0.5V to 6V
 DC Diode Current, I_{IK} (For $V_I < -0.5V$) -20mA
 DC Output Diode Current, I_{OK} (for $V_O < -0.5V$) -50mA
 DC Output Sink Current per Output Pin, I_O 70mA
 DC Output Source Current per Output Pin, I_O -30mA
 DC V_{CC} Current (I_{CC}) 264mA
 DC Ground Current (I_{GND}) 500mA

Thermal Information

Thermal Resistance (Typical, Note 2) θ_{JA} ($^{\circ}C/W$)
 SOIC Package 75
 Maximum Junction Temperature 150 $^{\circ}C$
 Maximum Storage Temperature Range -65 $^{\circ}C$ to 150 $^{\circ}C$
 Maximum Lead Temperature (Soldering 10s) 300 $^{\circ}C$
 (Lead Tips Only)

Operating Conditions

Operating Temperature Range, T_A 0 $^{\circ}C$ to 70 $^{\circ}C$
 Supply Voltage Range, V_{CC} 4.75V to 5.25V
 DC Input Voltage, V_I 0 to V_{CC}
 DC Output Voltage, V_O 0 to $\leq V_{CC}$
 Input Rise and Fall Slew Rate, dt/dv 0 to 10ns/V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications Commercial Temperature Range 0 $^{\circ}C$ to 70 $^{\circ}C$, V_{CC} Max = 5.25V, V_{CC} Min = 4.75V

| PARAMETER | SYMBOL | TEST CONDITIONS | | V _{CC} (V) | AMBIENT TEMPERATURE (T _A) | | | | UNITS |
|--|------------------|--|---------------------|---------------------|---------------------------------------|------|-------------|------|-------|
| | | V _I (V) | I _O (mA) | | 25°C | | 0°C TO 70°C | | |
| | | | | | MIN | MAX | MIN | MAX | |
| High Level Input Voltage | V _{IH} | | | 4.75 to 5.25 | 2 | - | 2 | - | V |
| Low Level Input Voltage | V _{IL} | | | 4.75 to 5.25 | - | 0.8 | - | 0.8 | V |
| High Level Output Voltage | V _{OH} | V _{IH} or V _{IL} | -15 | Min | 2.4 | - | 2.4 | - | V |
| Low Level Output Voltage | V _{OL} | V _{IH} or V _{IL} | 48 | Min | - | 0.55 | - | 0.55 | V |
| High Level Input Current | I _{IH} | V _{CC} | | Max | - | 0.1 | - | 1 | μA |
| Low Level Input Current | I _{IL} | GND | | Max | - | -0.1 | - | -1 | μA |
| Three State Leakage Current | I _{OZH} | V _{CC} | | Max | - | 0.5 | - | 10 | μA |
| | I _{OZL} | GND | | Max | - | -0.5 | - | -10 | μA |
| Input Clamp Voltage | V _{IK} | V _{CC} or GND | -18 | Min | - | -1.2 | - | -1.2 | V |
| Short Circuit Output Current (Note 3) | I _{OS} | V _O = 0 V _{CC} or GND | | Max | -75 | - | -75 | - | mA |
| Quiescent Supply Current, MSI | I _{CC} | V _{CC} or GND | 0 | Max | - | 8 | - | 80 | μA |
| Additional Quiescent Supply Current per Input Pin TTL Inputs High, 1 Unit Load | ΔI _{CC} | 3.4V (Note 4) | | Max | - | 1.6 | - | 1.6 | mA |

NOTES:

3. Not more than one output should be shorted at one time. Test duration should not exceed 100ms.
4. Inputs that are not measured are at V_{CC} or GND.
5. FCT Input Loading: All inputs are 1 unit load. Unit load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 1.6mA Max at 70 $^{\circ}C$.

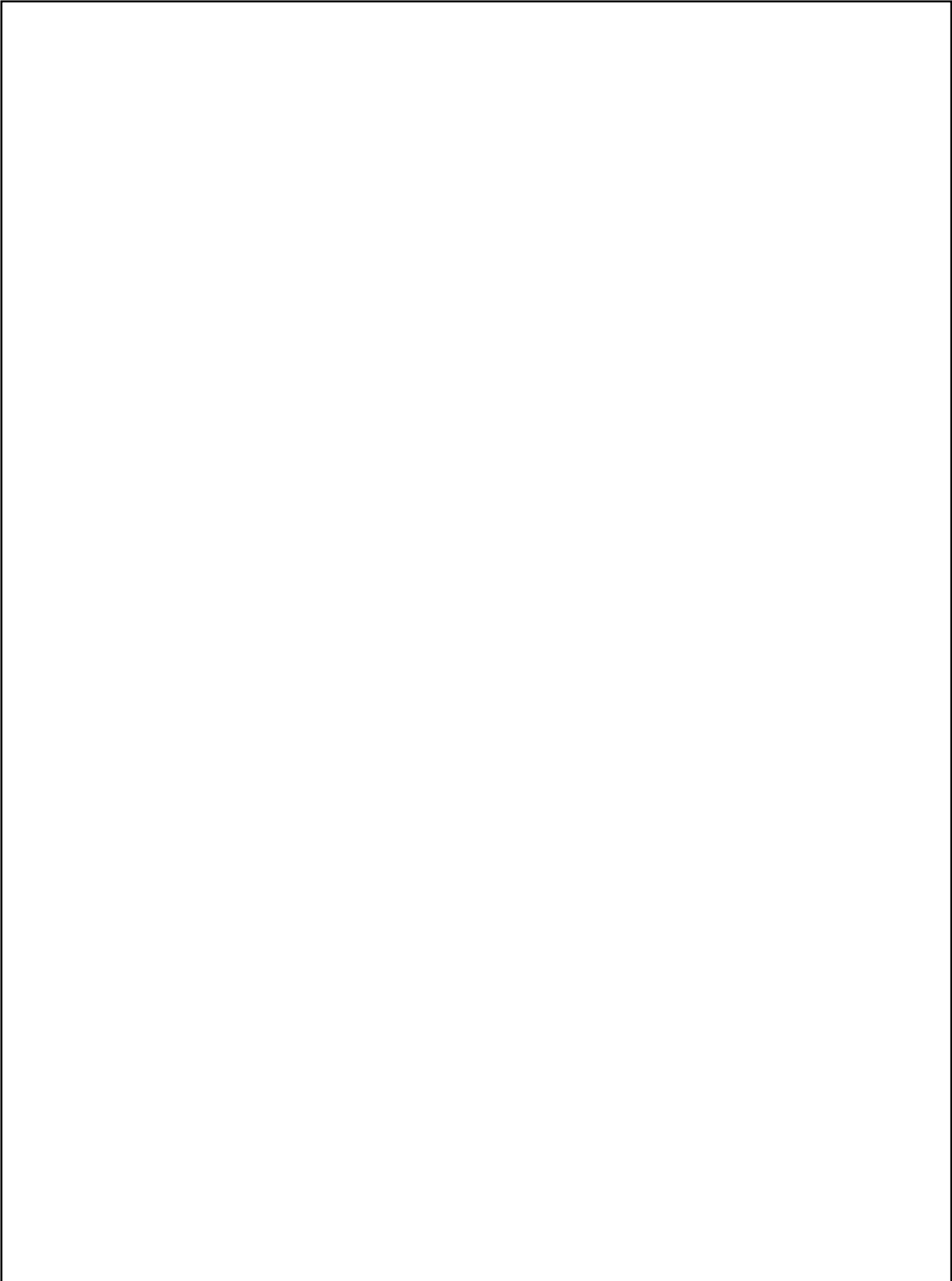
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Switching Specifications Over Operating Range FCT Series $t_r, t_f = 2.5\text{ns}$, $C_L = 50\text{pF}$, R_L (Figure 1)

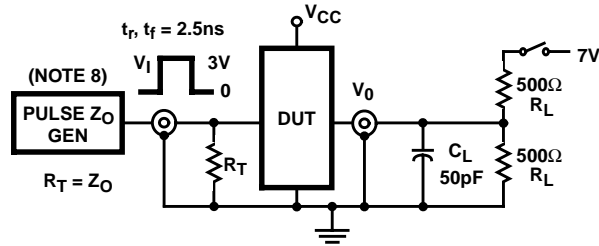
| PARAMETER | SYMBOL | V_{CC} (V) | 25°C | 0°C TO 70°C | | UNITS |
|--|----------------------|---------------|------|-------------|-----|-------|
| | | | TYP | MIN | MAX | |
| Propagation Delays | | | | | | |
| Data to Outputs | t_{PLH}, t_{PHL} | 5 (Note 6) | 6 | 1.5 | 8 | ns |
| Output Enable to Output | t_{PZL}, t_{PZH} | 5 | 9 | 1.5 | 12 | ns |
| Output Disable to Output | t_{PLZ}, t_{PHZ} | 5 | 7.5 | 1.5 | 10 | ns |
| Power Dissipation Capacitance | C_{PD} (Note 7) | - | - | - | - | pF |
| Minimum (Valley) V_{OHV} During Switching of Other Outputs (Output Under Test Not Switching) | V_{OHV} | 5 | 0.5 | - | - | V |
| Maximum (Peak) V_{OLP} During Switching of Other Outputs (Output Under Test Not Switching) | V_{OLP} | 5 | 1 | - | - | V |
| Input Capacitance | C_I | - | - | - | 10 | pF |
| Three-State Output Capacitance | C_O | - | - | - | 15 | pF |

NOTES:

6. 5V: Minimum is at 5.25V for 0°C to 70°C, Maximum is at 4.75V for 0°C to 70°C, Typical is at 5V.
7. C_{PD} , measured per flip-flop, is used to determine the dynamic power consumption.
 P_D (per package) = $V_{CC} I_{CC} + \Sigma(V_{CC}^2 f_I C_{PD} + V_O^2 f_O C_L + V_{CC} \Delta I_{CC} D)$ where:
 V_{CC} = supply voltage
 ΔI_{CC} = flow through current x unit load
 C_L = output load capacitance
 D = duty cycle of input high
 f_O = output frequency
 f_I = input frequency



Test Circuits and Waveforms



NOTE:

8. Pulse Generator for All Pulses: Rate $\leq 1.0\text{MHz}$; $Z_{OUT} \leq 50\Omega$;
 $t_r, t_f \leq 2.5\text{ns}$.

FIGURE 1. TEST CIRCUIT

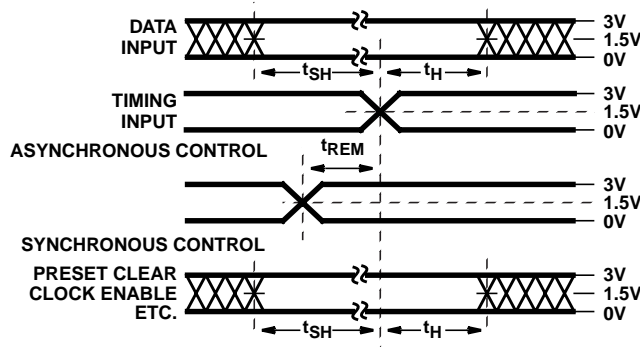


FIGURE 2. SETUP, HOLD, AND RELEASE TIMING

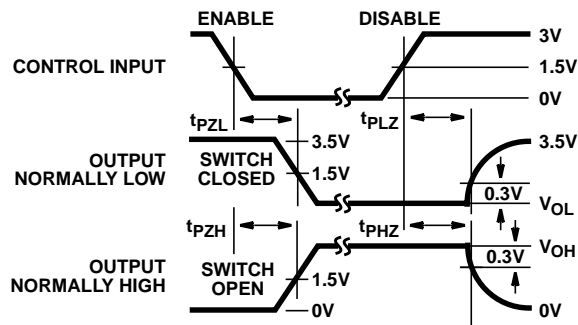


FIGURE 4. ENABLE AND DISABLE TIMING

| SWITCH POSITION | |
|--------------------------------------|--------|
| TEST | SWITCH |
| t_{PLZ}, t_{PZL} , Open Drain | Closed |
| $t_{PHZ}, t_{PZH}, t_{PLH}, t_{PHL}$ | Open |

DEFINITIONS:

C_L = Load capacitance, includes jig and probe capacitance.

R_T = Termination resistance, should be equal to Z_{OUT} of the Pulse Generator.

$V_{IN} = 0\text{V}$ to 3V .

Input: $t_r = t_f = 2.5\text{ns}$ (10% to 90%), unless otherwise specified

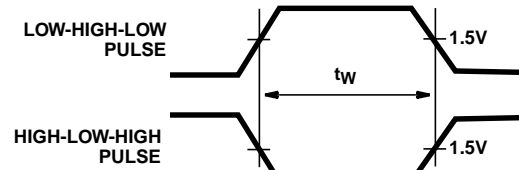


FIGURE 3. PULSE WIDTH

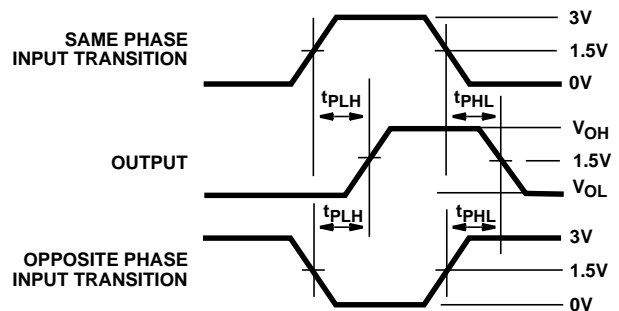
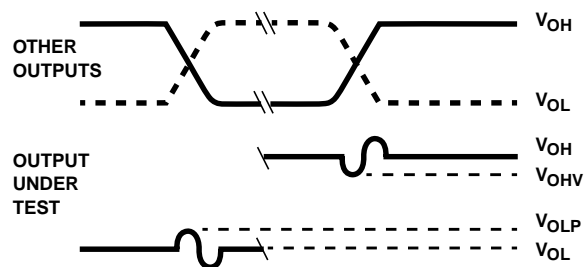


FIGURE 5. PROPAGATION DELAY

Test Circuits and Waveforms (Continued)



NOTES:

9. V_{OLP} is measured with respect to a ground reference near the output under test. V_{OHV} is measured with respect to V_{OH} .
10. Input pulses have the following characteristics:
 $PRR \leq 1\text{MHz}$, $t_r = 2.5\text{ns}$, $t_f = 2.5\text{ns}$, skew 1ns .
11. R.F. fixture with 700MHz design rules required. IC should be soldered into test board and bypassed with $0.1\mu\text{F}$ capacitor. Scope and probes require 700MHz bandwidth.

FIGURE 6. SIMULTANEOUS SWITCHING TRANSIENT WAVEFORMS

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